

Izabella Grzegory

List of Publications by Year in descending order

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443
all docs

443
docs citations

443
times ranked

5887
citing authors

#	ARTICLE	IF	CITATIONS
1	Recent Progress in Crystal Growth of Bulk GaN. Acta Physica Polonica A, 2022, 141, 167-174.	0.5	2
2	On Stress-Induced Polarization Effect in Ammonothermally Grown GaN Crystals. Crystals, 2022, 12, 554.	2.2	4
3	Nitrogen Dissolution in Liquid Ga and Fe: Comprehensive Ab Initio Analysis, Relevance for Crystallization of GaN. Materials, 2021, 14, 1306.	2.9	4
4	Critical Evaluation of Various Spontaneous Polarization Models and Induced Electric Fields in III-Nitride Multi-Quantum Wells. Materials, 2021, 14, 4935.	2.9	6
5	Adsorption of nitrogen at AlN(000-1) surface – Decisive role of structural and electronic factors. Surface Science, 2021, 713, 121891.	1.9	2
6	Experimental and theoretical evidence of the temperature-induced wurtzite to rocksalt phase transition in GaN under high pressure. Physical Review B, 2020, 102, .	3.2	15
7	Complex Geometric Structure of a Simple Solid-Liquid Interface: GaN(0001)-Ga. Physical Review Letters, 2020, 124, 086101.	7.8	6
8	Iron and manganese as dopants used in the crystallization of highly resistive HVPE-GaN on native seeds. Japanese Journal of Applied Physics, 2019, 58, SC1047.	1.5	23
9	Homoepitaxial growth by halide vapor phase epitaxy of semi-polar GaN on ammonothermal seeds. Japanese Journal of Applied Physics, 2019, 58, SC1030.	1.5	8
10	Catalytic Synthesis of Nitric Monoxide at the AlN(0001) Surface: Ab Initio Analysis. Journal of Physical Chemistry C, 2019, 123, 10893-10906.	3.1	4
11	Physical properties of Ga-Fe-N system relevant for crystallization of GaN – Initial studies. Journal of Crystal Growth, 2019, 507, 77-86.	1.5	1
12	Melting of tetrahedrally bonded semiconductors: –anomaly– of the phase diagram of GaN?. Journal of Crystal Growth, 2019, 505, 5-9.	1.5	7
13	Semi-insulating HVPE-GaN grown on native seeds (Conference Presentation). , 2019, , .		0
14	First Step in Exploration of Fe–Ga–N System for Efficient Crystallization of GaN at High Pressure. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700897.	1.8	2
15	Adsorption of N ₂ and H ₂ at AlN(0001) Surface: Ab Initio Assessment of the Initial Stage of Ammonia Catalytic Synthesis. Journal of Physical Chemistry C, 2018, 122, 20301-20311.	3.1	9
16	Correlating compositional, structural and optical properties of InGaN quantum wells by transmission electron microscopy. , 2018, , 267-272.		0
17	Diffusion of oxygen in bulk GaN crystals at high temperature and at high pressure. Journal of Crystal Growth, 2016, 449, 35-42.	1.5	8
18	Preparation of a smooth Ga–Gallium solid–liquid interface. Journal of Crystal Growth, 2016, 448, 70-75.	1.5	7

#	ARTICLE	IF	CITATIONS
19	HVPE-GaN growth on GaN-based advanced substrates by Smart Cut™. , 2016, , .		0
20	HVPE-GaN growth on GaN-based Advanced Substrates by Smart Cut™, ¢. Journal of Crystal Growth, 2016, 456, 73-79.	1.5	9
21	Homoepitaxial growth of HVPE-GaN doped with Si. Journal of Crystal Growth, 2016, 456, 91-96.	1.5	29
22	Growth of HVPE-GaN on native seeds â€“ numerical simulation based on experimental results. Journal of Crystal Growth, 2016, 456, 86-90.	1.5	9
23	Influence of crystallization front direction on the Mg-related impurity centers incorporation in bulk GaN:Mg grown by HNPS method. Optical Materials, 2016, 58, 491-496.	3.6	1
24	Influence of edge-grown HVPE GaN on the structural quality of c-plane oriented HVPE-GaN grown on ammonothermal GaN substrates. Journal of Crystal Growth, 2016, 456, 80-85.	1.5	18
25	High Temperature Stability of Electrical and Optical Properties of Bulk GaN:Mg Grown by HNPS Method in Different Crystallographic Directions. Acta Physica Polonica A, 2016, 129, A-126-A-128.	0.5	2
26	The challenge of decomposition and melting of gallium nitride under high pressure and high temperature. Journal of Physics and Chemistry of Solids, 2015, 85, 138-143.	4.0	34
27	Examination of defects and the seed's critical thickness in HVPEâ€“GaN growth on ammonothermal GaN seed. Physica Status Solidi (B): Basic Research, 2015, 252, 1172-1179.	1.5	26
28	Homoepitaxial HVPE GaN growth on non- and semi-polar seeds. Proceedings of SPIE, 2015, , .	0.8	4
29	Preparation of free-standing GaN substrates from GaN layers crystallized by hydride vapor phase epitaxy on ammonothermal GaN seeds. Japanese Journal of Applied Physics, 2014, 53, 05FA04.	1.5	21
30	HVPE-GaN grown on MOCVD-GaN/sapphire template and ammonothermal GaN seeds: Comparison of structural, optical, and electrical properties. Journal of Crystal Growth, 2014, 394, 55-60.	1.5	44
31	Trueâ€“blue laser diodes grown by plasmaâ€“assisted MBE on bulk GaN substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 666-669.	0.8	3
32	Examination of growth rate during hydride vapor phase epitaxy of GaN on ammonothermal GaN seeds. Journal of Crystal Growth, 2014, 407, 52-57.	1.5	21
33	HVPE-GaN growth on misoriented ammonothermal GaN seeds. Journal of Crystal Growth, 2014, 403, 32-37.	1.5	15
34	Structural defects in bulk GaN. Journal of Crystal Growth, 2014, 403, 66-71.	1.5	5
35	Homoepitaxial HVPE-GaN growth on non-polar and semi-polar seeds. Journal of Crystal Growth, 2014, 403, 48-54.	1.5	31
36	Photo-etching of HVPE-grown GaN: Revealing extended non-homogeneities induced by periodic carrier gas exchange. Journal of Crystal Growth, 2014, 403, 77-82.	1.5	8

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37	Role and influence of impurities on GaN crystal grown from liquid solution under high nitrogen pressure in multi-feed-seed configuration. Proceedings of SPIE, 2013, , .	0.8	6
38	True-blue nitride laser diodes grown by plasma assisted MBE on low dislocation density GaN substrates. Proceedings of SPIE, 2013, , .	0.8	0
39	Analysis of self-lift-off process during HVPE growth of GaN on MOCVD-GaN/sapphire substrates with photolithographically patterned Ti mask. Journal of Crystal Growth, 2013, 380, 99-105.	1.5	24
40	GaN doped with beryllium—An effective light converter for white light emitting diodes. Applied Physics Letters, 2013, 103, .	3.3	23
41	Preparation of Free-Standing GaN Substrates from Thick GaN Layers Crystallized by Hydride Vapor Phase Epitaxy on Ammonothermally Grown GaN Seeds. Applied Physics Express, 2013, 6, 075504.	2.4	51
42	Growth mechanisms in semipolar GaN. http://www.w3.org/1998/Math/MathML altimg="si0020.gif" overflow="scroll" <mml:mo stretchy="false">(</mml:mo> <mml:mn>2</mml:mn> <mml:mspace width=".5em") Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 547 Td (/> <mml:mn>2</mml:mn> <mml:mspace width=".5em")	1.5	20
43	HVPE-GaN growth on ammonothermal GaN crystals. Proceedings of SPIE, 2013, , .	0.8	10
44	Influence of substrate planar defects on MOVPE GaN layer growth. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 503-506.	1.8	1
45	Temperature-Dependence of Exciton Radiative Recombination in (Al,Ga)N/GaN Quantum Wells Grown on a-Plane GaN Substrates. Japanese Journal of Applied Physics, 2013, 52, 08JC01.	1.5	8
46	The homoepitaxial challenge: GaN crystals grown at high pressure for laser diodes and laser diode arrays. , 2013, , 18-77.		3
47	Nonlinear emission properties of an optically anisotropic GaN-based microcavity. Physical Review B, 2012, 86, .	3.2	5
48	The nature of Cr center in GaN: Magnetic anisotropy of GaN:Cr single crystals. Journal of Applied Physics, 2012, 112, 113914.	2.5	4
49	Characterization of the Nonpolar GaN Substrate Obtained by Multistep Regrowth by Hydride Vapor Phase Epitaxy. Applied Physics Express, 2012, 5, 011001.	2.4	6
50	Multi feed seed (MFS) high pressure crystallization of In^{2+} in GaN. Journal of Crystal Growth, 2012, 350, 5-10.	1.5	31
51	Growth of GaN:Mg crystals by high nitrogen pressure solution method in multi-feed—seed configuration. Journal of Crystal Growth, 2012, 350, 50-55.	1.5	15
52	Imaging extended non-homogeneities in HVPE grown GaN with Kelvin Probe Microscopy and photo-etching. Journal of Crystal Growth, 2012, 353, 68-71.	1.5	5
53	Thermal carrier emission and nonradiative recombinations in nonpolar (Al,Ga)N/GaN quantum wells grown on bulk GaN. Journal of Applied Physics, 2012, 111, 033517.	2.5	10
54	Unambiguous relationship between photoluminescence energy and its pressure evolution in InGaN/GaN quantum wells. Physica Status Solidi (B): Basic Research, 2012, 249, 476-479.	1.5	1

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73	Tilt of InGaN layers on miscut GaN substrates. <i>Physica Status Solidi - Rapid Research Letters</i> , 2010, 4, 142-144.	2.4	12
74	Degradation Mechanisms of InGaN Laser Diodes. <i>Proceedings of the IEEE</i> , 2010, 98, 1214-1219.	21.3	19
75	High temperature chemical and physical changes of the HVPE-prepared GaN semiconductor. <i>Materials Chemistry and Physics</i> , 2010, 122, 537-543.	4.0	9
76	Ca ₃ N ₂ as a flux for crystallization of GaN. <i>Journal of Crystal Growth</i> , 2010, 312, 2574-2578.	1.5	3
77	The influence of indium on the growth of GaN from solution under high pressure. <i>Journal of Crystal Growth</i> , 2010, 312, 2593-2598.	1.5	4
78	Revealing extended defects in HVPE-grown GaN. <i>Journal of Crystal Growth</i> , 2010, 312, 2611-2615.	1.5	25
79	Hole carrier concentration and photoluminescence in magnesium doped InGaN and GaN grown on sapphire and GaN misoriented substrates. <i>Journal of Applied Physics</i> , 2010, 108, 023516.	2.5	17
80	Growth of Bulk GaN Crystals by HVPE on Single Crystalline GaN Seeds. <i>Springer Series in Materials Science</i> , 2010, , 61-78.	0.6	6
81	High Pressure Solution Growth of Gallium Nitride. <i>Springer Series in Materials Science</i> , 2010, , 207-234.	0.6	15
82	Application of a composite plasmonic substrate for the suppression of an electromagnetic mode leakage in InGaN laser diodes. <i>Applied Physics Letters</i> , 2009, 95, .	3.3	36
83	Different pressure behavior of GaN/AlGaIn quantum structures grown along polar and nonpolar crystallographic directions. <i>Journal of Applied Physics</i> , 2009, 105, .	2.5	20
84	MAGNETO-LUMINESCENCE OF GADOLINIUM DOPED GALLIUM NITRIDE. <i>International Journal of Modern Physics B</i> , 2009, 23, 2994-2998.	2.0	1
85	Nitride-based quantum structures and devices on modified GaN substrates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009, 206, 1130-1134.	1.8	17
86	Bulk GaN crystals and wafers grown by HVPE without intentional doping. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, S297-S300.	0.8	11
87	What is new in nitride laser diodes reliability studies. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, S881.	0.8	0
88	InGaIn light emitting diodes for 415 nm–520 nm spectral range by plasma assisted MBE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, S917.	0.8	32
89	Carrier recombination under one-photon and two-photon excitation in GaN epilayers. <i>Micron</i> , 2009, 40, 118-121.	2.2	2
90	Structural defects in GaN crystals grown by HVPE on needle-shaped GaN seeds obtained under high N ₂ pressure. <i>Journal of Crystal Growth</i> , 2009, 311, 1407-1410.	1.5	1

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91	Nitride-based laser diodes by plasma-assisted MBE—From violet to green emission. Journal of Crystal Growth, 2009, 311, 1632-1639.	1.5	45
92	Influence of substrate misorientation on properties of InGaN layers grown on freestanding GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1485-1487.	0.8	12
93	Liquid phase epitaxy of GaN on MOCVD GaN/sapphire and HVPE free-standing substrates under high nitrogen pressure. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1539-1542.	0.8	1
94	Optically pumped lasing of GaN/AlGaIn structures grown along a non-polar crystallographic direction. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2173-2175.	0.8	1
95	High rate photoelectrochemical etching of GaN and the use of patterned substrates for HVPE regrowth. Journal of Crystal Growth, 2008, 310, 3478-3481.	1.5	4
96	Fabrication and properties of GaN-based lasers. Journal of Crystal Growth, 2008, 310, 3979-3982.	1.5	12
97	Growth of InGaIn and InGaIn/InGaIn quantum wells by plasma-assisted molecular beam epitaxy. Journal of Crystal Growth, 2008, 310, 3983-3986.	1.5	35
98	GaN crystallization by the high-pressure solution growth method on HVPE bulk seed. Journal of Crystal Growth, 2008, 310, 3924-3933.	1.5	35
99	Why InGaIn laser-diode degradation is accompanied by the improvement of its thermal stability. Proceedings of SPIE, 2008, , .	0.8	9
100	Nonradiative recombination at threading dislocations in n-type GaN: Studied by cathodoluminescence and defect selective etching. Applied Physics Letters, 2008, 92, .	3.3	74
101	Substrate misorientation induced strong increase in the hole concentration in Mg doped GaN grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2008, 93, 172117.	3.3	31
102	16 nm tuning range of blue InGaIn laser diodes achieved by 200 K temperature increase. Proceedings of SPIE, 2008, , .	0.8	0
103	Secrets of GaN substrates properties for high luminosity of InGaIn quantum wells. Proceedings of SPIE, 2008, , .	0.8	1
104	Time-Resolved Studies of Gallium Nitride Doped with Gadolinium. Acta Physica Polonica A, 2008, 114, 1425-1430.	0.5	2
105	LASER DIODES GROWN ON BULK GALLIUM NITRIDE SUBSTRATES. , 2008, , 223-252.		0
106	Comparison of gain in group-III-nitride laser structures grown by metalorganic vapour phase epitaxy and plasma-assisted molecular beam epitaxy on bulk GaN substrates. Semiconductor Science and Technology, 2007, 22, 736-741.	2.0	3
107	Optically pumped GaN/AlGaIn separate-confinement heterostructure laser grown along the (112̄0) nonpolar direction. Applied Physics Letters, 2007, 90, 081104.	3.3	15
108	Strain-compensated AlGaIn/GaN/InGaIn cladding layers in homoepitaxial nitride devices. Applied Physics Letters, 2007, 91, .	3.3	14

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109	Correlation between luminescence and compositional striations in InGaN layers grown on miscut GaN substrates. Applied Physics Letters, 2007, 91, .	3.3	37
110	MnAsdots grown onGaN(0001 \hat{A}) \hat{a} ^(1 \hat{A} –1)surface. Physical Review B, 2007, 75, .	3.2	0
111	Mode dynamics of high power (InAl)GaN based laser diodes grown on bulk GaN substrate. Journal of Applied Physics, 2007, 101, 083109.	2.5	16
112	Continuous-Wave Operation of Blue InGaN Laser Diodes Made by Plasma-Assisted MBE. AIP Conference Proceedings, 2007, , .	0.4	0
113	MnAs dots on GaN(0001 \hat{A} ,,) surface \hat{a} €” growth process and electronic structure. AIP Conference Proceedings, 2007, , .	0.4	0
114	Comprehensive study of reliability of InGaN-based laser diodes. , 2007, , .		1
115	Tunable broad-area InGaN laser diodes in external cavity. , 2007, , .		2
116	Comparison of optical properties of InGaN/GaN/AlGaN laser structures grown by MOVPE and MBE. , 2007, , .		0
117	Diluted Magnetic III-V Semiconductors With Mn For Possible Spintronic Applications. AIP Conference Proceedings, 2007, , .	0.4	0
118	Tunneling in dislocation-free GaN/AlGaN double-barrier diodes grown on bulk GaN. AIP Conference Proceedings, 2007, , .	0.4	2
119	Modelling the growth of nitrides in ammonia \hat{a} €”rich environment. Crystal Research and Technology, 2007, 42, 1281-1290.	1.3	12
120	Magneto-optical studies of iron impurity in HVPE GaN. Physica B: Condensed Matter, 2007, 401-402, 458-461.	2.7	3
121	Crystallization of low dislocation density GaN by high-pressure solution and HVPE methods. Journal of Crystal Growth, 2007, 300, 17-25.	1.5	29
122	Adsorption and dissolution of nitrogen in lithium \hat{a} €”QM DFT investigation. Journal of Crystal Growth, 2007, 304, 299-309.	1.5	0
123	Platelets and needles: Two habits of pressure-grown GaN crystals. Journal of Crystal Growth, 2007, 305, 414-420.	1.5	8
124	Orthodox etching of HVPE-grown GaN. Journal of Crystal Growth, 2007, 305, 384-392.	1.5	113
125	Role of dislocation-free GaN substrates in the growth of indium containing optoelectronic structures by plasma-assisted MBE. Journal of Crystal Growth, 2007, 305, 346-354.	1.5	20
126	High pressure \hat{a} €”high temperature seeded growth of GaN on 1 in sapphire/GaN templates: Analysis of convective transport. Journal of Crystal Growth, 2007, 307, 259-267.	1.5	21

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127	Optical gain and saturation behavior in homoepitaxially grown InGaN/GaN/AlGaIn laser structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007, 4, 82-85.	0.8	1
128	Platelets and needles: two habits of pressure grown GaN crystals. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007, 4, 2236-2239.	0.8	1
129	Capture kinetics at deep-level electron traps in GaN-based laser diode. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007, 4, 2878-2882.	0.8	7
130	Gain mechanisms in field-free InGaIn layers grown on sapphire and bulk GaN substrate. <i>Physica Status Solidi - Rapid Research Letters</i> , 2007, 1, 141-143.	2.4	3
131	Deep-Level Defects in MBE-Grown GaN-Based Laser Structure. <i>Acta Physica Polonica A</i> , 2007, 112, 331-337.	0.5	2
132	Optically Pumped Laser Action on Nitride Based Separate Confinement Heterostructures Grown along the (11 $\bar{1}$ 20) Crystallographic Direction. <i>Acta Physica Polonica A</i> , 2007, 112, 467-472.	0.5	0
133	Magnetoluminescence Studies of GaN:Fe. <i>Acta Physica Polonica A</i> , 2007, 112, 177-182.	0.5	0
134	Effect of high-temperature annealing on the residual strain and bending of freestanding GaN films grown by hydride vapor phase epitaxy. <i>Applied Physics Letters</i> , 2006, 88, 141909.	3.3	30
135	Anomalous temperature characteristics of single wide quantum well InGaIn laser diode. <i>Applied Physics Letters</i> , 2006, 88, 071121.	3.3	22
136	Negative differential resistance in dislocation-free GaN \cdot AlGaIn double-barrier diodes grown on bulk GaN. <i>Applied Physics Letters</i> , 2006, 88, 172106.	3.3	99
137	GaN surface doped with Fe atoms. <i>Journal of Alloys and Compounds</i> , 2006, 423, 136-138.	5.5	3
138	Growth and characterization of AlInN/GaInN quantum wells for high-speed intersubband devices at telecommunication wavelengths. , 2006, , .		5
139	Growth of bulk GaN by HVPE on pressure grown seeds. , 2006, , .		12
140	Load dislocation density broad area high power CW operated InGaIn laser diodes. , 2006, 6184, 139.		0
141	Growth of GaN on patterned GaN/sapphire substrates with various metallic masks by high pressure solution method. , 2006, , .		3
142	Broad-area high-power CW operated InGaIn laser diodes. , 2006, 6133, 168.		7
143	Reliability of InGaIn laser diodes grown on low dislocation density bulk GaN substrates. , 2006, 6184, 131.		0
144	High-Pressure Crystallization of GaN. , 2006, , 1-43.		0

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145	Crystallization of free standing bulk GaN by HVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1453-1456.	0.8	9
146	Growth of GaN on patterned thick HVPE free standing GaN substrates by high pressure solution method. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1487-1490.	0.8	1
147	Barrier-to-well carrier dynamics of InGaN/GaN multi-quantum-wells grown by plasma assisted MBE on bulk GaN substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1962-1965.	0.8	1
148	Screening of polarization induced electric fields in blue/violet InGaN/GaN laser diodes by Si doping in quantum barriers revealed by hydrostatic pressure. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 2303-2306.	0.8	3
149	Optical properties of InGaN/GaN quantum wells on sapphire and bulk GaN substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 2078-2081.	0.8	1
150	Mass flow and reaction analysis of the growth of GaN by HVPE. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 131-134.	1.8	2
151	Crystallization of GaN by HVPE on pressure grown seeds. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 1654-1657.	1.8	7
152	Towards identification of degradation mechanisms in InGaN laser diodes grown on bulk GaN crystals. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 1778-1782.	1.8	5
153	Role of band potential roughness on the luminescence properties of InGaN quantum wells grown by MBE on bulk GaN substrates. Physica Status Solidi (B): Basic Research, 2006, 243, 1614-1618.	1.5	6
154	Etching, Raman and PL study of thick HVPE-grown GaN. Materials Science in Semiconductor Processing, 2006, 9, 175-179.	4.0	14
155	Selective etching of dislocations in violet-laser diode structures. Journal of Crystal Growth, 2006, 293, 18-21.	1.5	15
156	CFD and reaction computational analysis of the growth of GaN by HVPE method. Journal of Crystal Growth, 2006, 296, 31-42.	1.5	23
157	Atomically flat GaMnN by diffusion of Mn into GaN(). Superlattices and Microstructures, 2006, 40, 607-611.	3.1	7
158	Resonant photoemission study of Ti interaction with GaN surface. Surface Science, 2006, 600, 873-879.	1.9	3
159	Growth of thin AlInN ^x GaN quantum wells for applications to high-speed intersubband devices at telecommunication wavelengths. Journal of Vacuum Science & Technology B, 2006, 24, 1505.	1.3	29
160	Carrier recombination and diffusion in GaN revealed by transient luminescence under one-photon and two-photon excitations. Applied Physics Letters, 2006, 89, 172119.	3.3	18
161	60mW continuous-wave operation of InGaN laser diodes made by plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2006, 88, 221108.	3.3	48
162	Degradation mechanisms in InGaN laser diodes grown on bulk GaN crystals. Applied Physics Letters, 2006, 88, 201111.	3.3	75

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163	Crack Free GaInN/AlInN Multiple Quantum Wells Grown on GaN with Strong Intersubband Absorption at 1.55 μ m. Acta Physica Polonica A, 2006, 110, 175-181.	0.5	3
164	Photoluminescence and Electron Paramagnetic Resonance Studies of Bulk GaN Doped with Gadolinium. Acta Physica Polonica A, 2006, 110, 243-248.	0.5	14
165	High Power Continuous Wave Blue InAlGaN Laser Diodes Made by Plasma Assisted MBE. Acta Physica Polonica A, 2006, 110, 345-351.	0.5	1
166	Properties of violet laser diodes grown on bulk GaN substrates. , 2005, , .		4
167	Growth of AlN, GaN and InN from the solution. International Journal of Materials and Product Technology, 2005, 22, 226.	0.2	19
168	Gallium nitride growth on sapphire/GaN templates at high pressure and high temperatures. Journal of Crystal Growth, 2005, 274, 55-64.	1.5	19
169	Growth of GaN on patterned GaN/sapphire substrates by high pressure solution method. Journal of Crystal Growth, 2005, 281, 11-16.	1.5	10
170	Properties of InGaN blue laser diodes grown on bulk GaN substrates. Journal of Crystal Growth, 2005, 281, 107-114.	1.5	8
171	Defects in GaN single crystals and homoepitaxial structures. Journal of Crystal Growth, 2005, 281, 135-142.	1.5	26
172	Influence of dislocation and ionized impurity scattering on the electron mobility in GaN/AlGaN heterostructures. Journal of Crystal Growth, 2005, 281, 194-201.	1.5	9
173	Deposition of thick GaN layers by HVPE on the pressure grown GaN substrates. Journal of Crystal Growth, 2005, 281, 38-46.	1.5	66
174	Selective etching and TEM study of inversion domains in Mg-doped GaN epitaxial layers. Journal of Crystal Growth, 2005, 282, 45-48.	1.5	14
175	Surface and electronic structure of Ga _{0.92} In _{0.08} N thin film investigated by photoelectron spectroscopy. Thin Solid Films, 2005, 476, 396-404.	1.8	1
176	Resonant shake-up satellites in photoemission at the Ga 3p photothreshold in GaN. Solid State Communications, 2005, 136, 191-195.	1.9	4
177	Bowing of epitaxial layers grown on bulk GaN substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 1259-1264.	0.8	1
178	Microstructure of III-N semiconductors related to their applications in optoelectronics. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 1366-1373.	0.8	1
179	Anomalous behaviour of the photoluminescence from GaN/AlGaIn quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 1010-1013.	0.8	2
180	Screening of built-in electric fields in group III-nitride laser diodes observed by means of hydrostatic pressure. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 1019-1022.	0.8	1

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181	Bowing of GaN bulk crystals with mismatched epitaxial structures of (AlInGa)N. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005, 2, 1031-1034.	0.8	2
182	Localization Effects in InGaN/GaN Double Heterostructure Laser Diode Structures Grown on Bulk GaN Crystals. <i>Japanese Journal of Applied Physics</i> , 2005, 44, 7244-7249.	1.5	2
183	Neutral Mn Acceptor in GaN Studied in High Magnetic Fields. <i>AIP Conference Proceedings</i> , 2005, , .	0.4	0
184	Microstructure of InGaN quantum wells grown on GaN single crystals and sapphire. <i>Journal Physics D: Applied Physics</i> , 2005, 38, A89-A92.	2.8	1
185	Efficient radiative recombination and potential profile fluctuations in low-dislocation InGa _N /Ga _N multiple quantum wells on bulk GaN substrates. <i>Journal of Applied Physics</i> , 2005, 97, 103507.	2.5	22
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